

TECHNICAL SPECIFICATION

**Nanomanufacturing - Key control characteristics -
Part 6-33: Graphene-related products - Defect density of graphene: electron
energy loss spectroscopy**

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INTERNATIONAL ELECTROTECHNICAL COMMISSION

Nanomanufacturing - Key control characteristics - Part 6-33: Graphene-related products - Defect density of graphene: electron energy loss spectroscopy

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The text of this Technical Specification is based on the following documents:

Draft	Report on voting
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Full information on the voting for its approval can be found in the report on voting indicated in the above table.

The language used for the development of this Technical Specification is English.